

IGBT MODULE (F series)

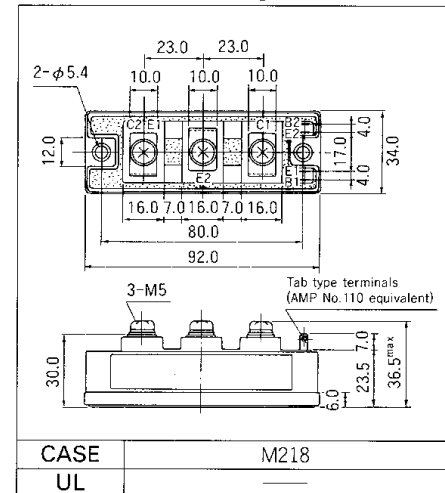
■ Features

- Low Saturation Voltage
- Voltage Drive
- Variety of Power Capacity Series

■ Applications

- Inverter for Motor Drive
- AC and DC Servo Drive Amplifier
- Uninterruptible Power Supply
- Industrial Machines, such as Welding Machines

■ Outline Drawings



■ Maximum Ratings and Characteristics

● Absolute Maximum Ratings

Items	Symbols	Ratings	Units
Collector-Emitter Voltage	V_{CES}	600	V
Gate-Emitter Voltage	V_{GES}	± 20	V
Collector Current	Continuous	I_C	100
	1ms	$I_{C \text{ pulse}}$	200
	Continuous	$-I_C$	100
	1ms	$-I_{C \text{ pulse}}$	200
Max. Power Dissipation	P_C	360	W
Operating Temperature	T_j	+150	$^{\circ}\text{C}$
Storage Temperature	T_{stg}	-40 to +125	$^{\circ}\text{C}$
Net. Weight		185	g
Isolation Voltage	AC, 1min.	V_{isol}	2500
Screw Torque	Mounting *1	3.5 [35]	N · m
	Terminals *1	3.5 [35]	(kg · cm)

*1 Recommendable Value 2.5 to 3.5 N·m { 25 to 35 kg·cm } (M5)

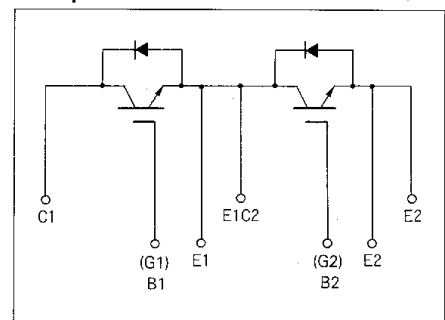
● Electrical Characteristics ($T_c=25^{\circ}\text{C}$)

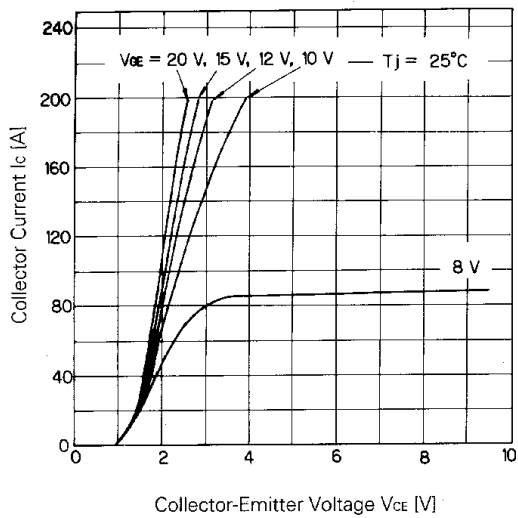
Items	Symbols	Test Conditions	Min.	Typ.	Max.	Units
Zero Gate Voltage Collector Current	I_{CES}	$V_{GE}=0\text{V } V_{CE}=600\text{V } T_j=25^{\circ}\text{C}$			1.0	mA
		$V_{GE}=0\text{V } V_{CE}=600\text{V } T_j=125^{\circ}\text{C}$			—	mA
Gate-Emitter Leakage Current	I_{GES}	$V_{CE}=0\text{V } V_{GE}=\pm 20\text{V}$			100	nA
Gate-Emitter Threshold Voltage	$V_{GE(th)}$	$V_{CE}=20\text{V } I_C=100\text{mA}$	3.0		6.0	V
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$V_{GE}=15\text{V } I_C=100\text{A}$			2.5	V
Input Capacitance	C_{ies}	$V_{GE}=0\text{V}$		9500		pF
Output Capacitance	C_{oes}	$V_{CE}=10\text{V}$		—		
Reverse Transfer Capacitance	C_{res}	$f=1\text{MHz}$		—		
Turn-on Time	t_{on}	$V_{CC}=300\text{V}$			0.8	μs
	t_r	$I_C=100\text{A}$			0.6	
Turn-off Time	t_{off}	$V_{GE}=\pm 15\text{V}$			1.5	
	t_f	$R_G=25\Omega$			1.0	
Diode Forward On-Voltage	V_F	$I_F=100\text{A}, V_{GE}=0\text{V}$			2.5	V
Reverse Recovery Time	t_{rr}	$I_F=100\text{A}, -di/dt=300\text{A}/\mu\text{s } V_{GE}=-10\text{V}$			300	ns

● Thermal Characteristics

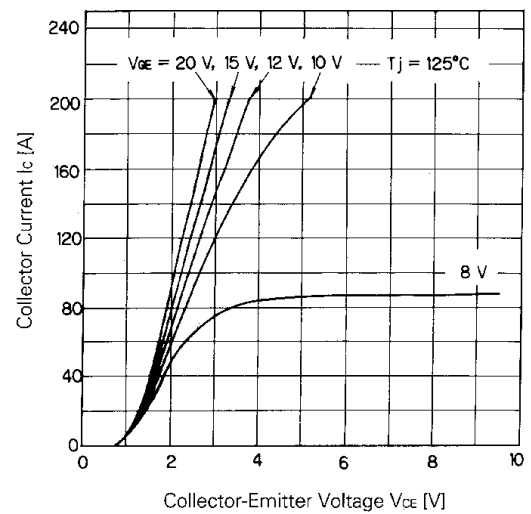
Items	Symbols	Test Conditions	Min.	Typ.	Max.	Units
Thermal Resistance	$R_{th(j-c)}$	IGBT			0.347	$^{\circ}\text{C/W}$
	$R_{th(j-e)}$	Diode			0.666	
	$R_{th(c-f)}$	With Thermal compound		0.05		

■ Equivalent Circuit Schematic

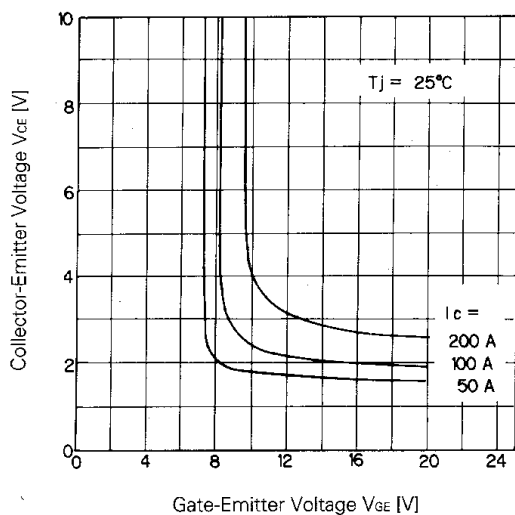




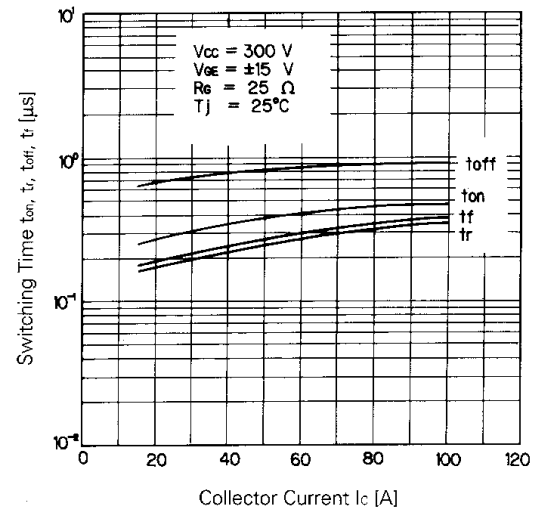
Collector Current vs. Collector-Emitter Voltage



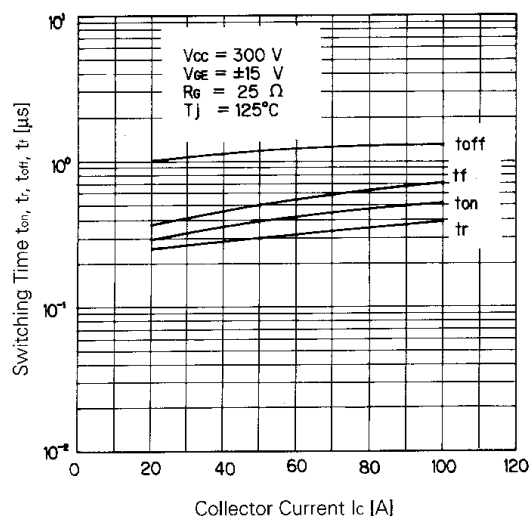
Collector Current vs. Collector-Emitter Voltage



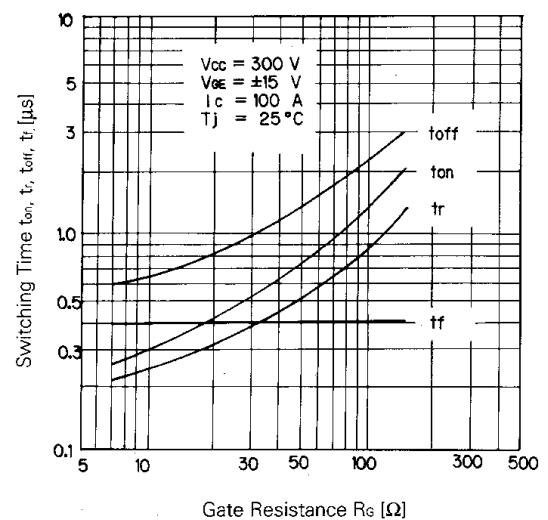
Collector-Emitter Voltage vs. Gate-Emitter Voltage



Switching Time



Switching Time



Switching Time-Gate Resistance

